# 45 V, 100 mA PNP general-purpose transistors Rev. 1 — 21 February 2012

Product data sheet

## **Product profile**

## 1.1 General description

PNP general-purpose transistors in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package	Package		
	NXP	JEITA	JEDEC	
BC857AMB	SOT883B	-	-	BC847AMB
BC857BMB	SOT883B	-	-	BC847BMB
BC857CMB	SOT883B	-	-	BC847CMB

#### 1.2 Features and benefits

- Leadless ultra small SMD plastic
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

## 1.3 Applications

- General-purpose switching and amplification
- Mobile applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-45	V
I <sub>C</sub>	collector current		-	-	-100	mΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$				
	BC857AMB		125	-	250	
	BC857BMB		220	-	475	
	BC857CMB		420	-	800	



# 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	1 3	3 
3	collector	23	1—
		Transparent	2
		top view	_
			sym013

## 3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BC857xMB series	-	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.37 mm	SOT883B		

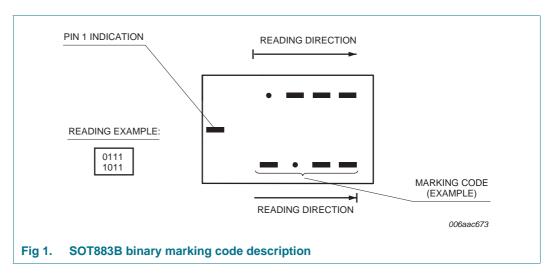
## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
BC857AMB	0100 0100
BC857BMB	0100 0101
BC857CMB	0100 0110

<sup>[1]</sup> For SOT883B binary marking code description, see Figure 1.

## 4.1 Binary marking code description



BC857XMB\_SER

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-45	V
$V_{EBO}$	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1][2]	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

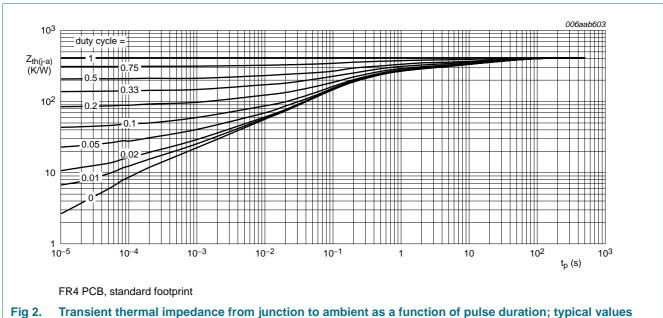
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

## Thermal characteristics

Table 7. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] -	-	500	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

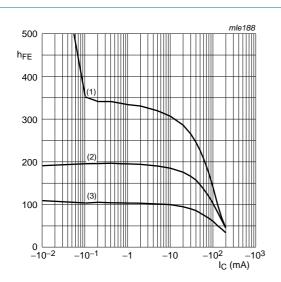
## 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	<b>-5</b>	μА
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$				
	BC857AMB	BC857AMB	125	-	250	
	BC857BMB	57BMB	220	-	475	
	BC857CMB		420	-	800	
V <sub>CEsat</sub>	V <sub>CEsat</sub> collector-emitter	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-200	mV
	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	[1] _	-	-400	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-	-820	mV
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.5	pF
NF	noise figure	$I_{C} = -200 \ \mu A; \ V_{CE} = -5 \ V; \ R_{S} = 2 \ k\Omega; \ f = 1 \ kHz; \ B = 200 \ Hz$	-	-	10	dB

<sup>[1]</sup> Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 



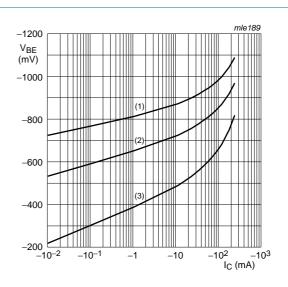
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 3. BC857AMB: DC current gain as a function of collector current; typical values



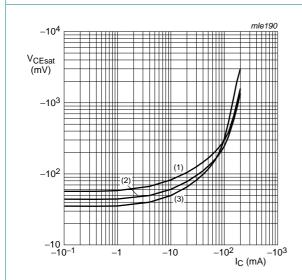
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 4. BC857AMB: Base-emitter voltage as a function of collector current; typical values



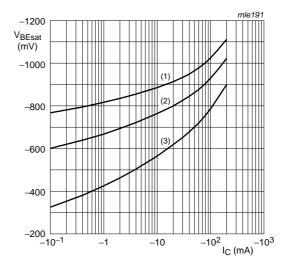
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. BC857AMB: Collector-emitter saturation voltage as a function of collector current; typical values



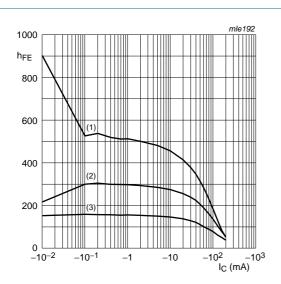
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 6. BC857AMB: Base-emitter saturation voltage as a function of collector current; typical values



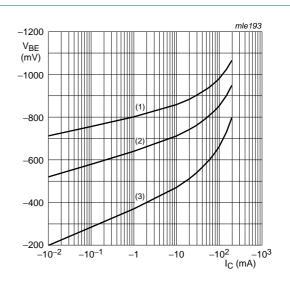
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. BC857BMB: DC current gain as a function of collector current; typical values



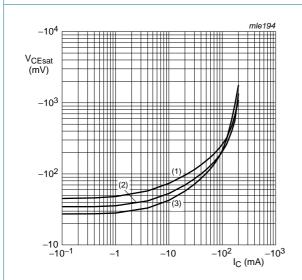
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. BC857BMB: Base-emitter voltage as a function of collector current; typical values



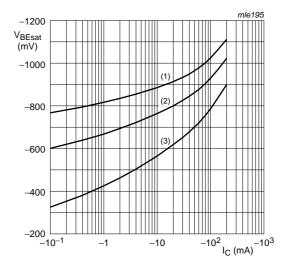


(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 9. BC857BMB: Collector-emitter saturation voltage as a function of collector current; typical values



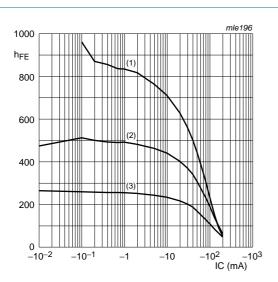
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 10. BC857BMB: Base-emitter saturation voltage as a function of collector current; typical values



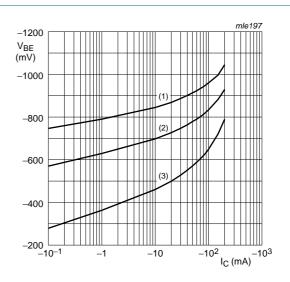
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 11. BC857CMB: DC current gain as a function of collector current; typical values



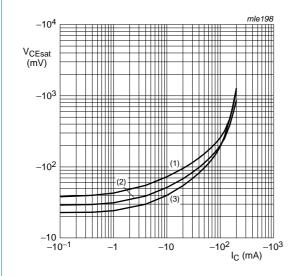
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 12. BC857CMB: Base-emitter voltage as a function of collector current; typical values



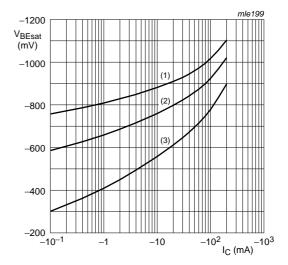
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 13. BC857CMB: Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

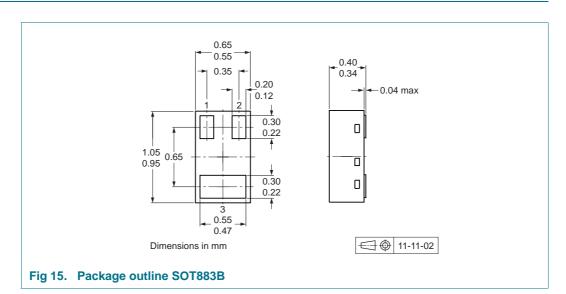
Fig 14. BC857CMB: Base-emitter saturation voltage as a function of collector current; typical values

## 8. Test information

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

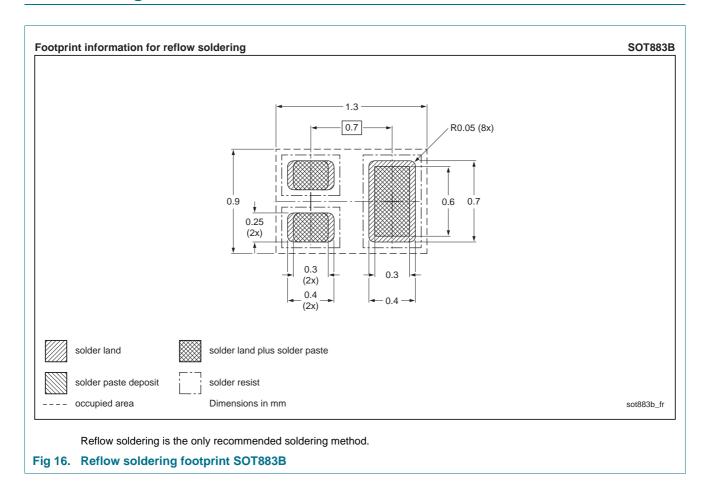
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
BC857xMB series	SOT883B	2 mm pitch, 8 mm tape and reel	-315

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

## 11. Soldering



45 V, 100 mA PNP general-purpose transistors

# 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC857XMB_SER v.1	20120221	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### 45 V, 100 mA PNP general-purpose transistors

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## 45 V, 100 mA PNP general-purpose transistors

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